외부 보강된 Bi-2223테이프의 가압 LN_2 하에서 임계전류 열화거동의 굽힘변형률 의존성

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Bending strain dependence of the critical current degradation behavior in externally-reinforced Bi-2223 tapes with different hermeticity under pressurized liquid nitrogen

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Abstract: The I_c degradation behaviors of externally-reinforced Bi-2223 superconducting tapes under pressurized liquid nitrogen were investigated. Tapes with different thickness of reinforcement layers were compared and the results showed that when the bending strain was calculated at the outer surface, the tape with the thicker reinforcement showed a better bending strain tolerance of I_c, but when the bending strain was calculated at the outermost filament, the I_c degradation behavior became identical for all tapes. I_{c0} decreased with the increase of applied pressure. After depressurization to atmospheric pressure from 1 MPa, the I_c was completely recovered to its initial values. Ballooning occurred after a thermal cycle.

Key Words: Bi-2223 tapes, Bending strain, Critical current, Pressurized LN2, External Reinforcement

1. Introduction

For practical applications such as power cables adopting Bi-2223 tapes, the tapes are subjected to various stresses and strains during fabrication and operation [1]. The influence of pressurization on the transport property of Bi-2223 tapes should also be considered [2]. Here, the influences of pressurization of LN_2 on the transport property of externally-reinforced Bi-2223 tapes at bent state were investigated.

2. Experimental Procedure

Three kinds of commercially-available and externally-reinforced Bi-2223 tapes fabricated using the powder-in-tube process were supplied. Table 1 lists the properties of the samples used and the cross-sections are shown in Fig. 1.

For bending tests under pressurized LN_2 , a ρ -shaped sample holder and a cryostat for pressurization were used as shown in Fig. 2. The test procedures and set-up for the pressurized bending tests were described in Ref. [2].

The nominal bending strain of the tape, ε_b , in a bent position on the mandrel is given in Eq. (1) and was defined at the outer surface of the sample.

$$\epsilon_b = \frac{t}{2R + t} \times 100\% \tag{1}$$

where t is the sample thickness, R is the bending radius at each voltage separation corresponding to a specific bending strain [1,2].

3. Results and Discussion

At atmospheric pressure, the I_c degradation behavior of the samples with bending strain are

Table 1 Specifications of Bi-2223 tapes

	ERT	HST1	HST2
Dimension (mm)	4.2 x 0.3	4.2 x 0.38	4.2 x 0.38
L ₄ at 77K (A)	138	133	155
Reinforcement material	Stainless steel	Brass	Brass
Reinforcement	40	80	80
thickness (µm)			
Multi-filament bundle	0.19	0.19	0.19
layer thickness (mm)			
Hermetic Sealing	None	One side	Both sides

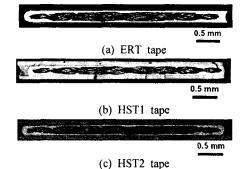


Fig. 1 Cross-sectional views of Bi-2223 tapes

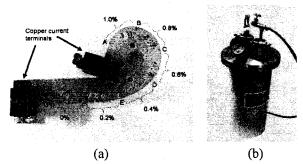


Fig. 2 Devices used to measure I_c - ϵ_b relationship under pressurized LN_2 . (a) A sample holder which gives a series of bending strains to HTS tapes, (b) View of the cryostat assembly.

shown in Fig 3. The HST tapes showed a better bending strain tolerance as compared with the ERT tape. The critical bending strains, $\epsilon_{irr.}$, which was defined as the strain for 95% I_c retention are 0.71%, 0.88%, and 0.89% for the ERT, HST1, and HST2 tapes, respectively. This is due to the thicker foils laminated on the HST tapes.

The bending strain at the outermost filament in all samples was also calculated by using Eq. 1 and Table 1. It can be seen that the ϵ_{iir} at the outermost filament responsible for I_c degradation became identical for all tapes, i.e., ϵ_{iir} =0.44%.

Figs. 4 shows the I_c degradation behavior with bending strain at LN_2 pressurized to 1 MPa for the HST2 tape. Ic degradation curves for the ERT and HST1 tape is not shown for brevity. All tapes showed a pressure-dependent I_c degradation behavior. It was observed that the I_c at the unstrained state, I_{c0} , at 1 MPa for all samples were decreased by over 40% when compared with the case at atmospheric conditions.

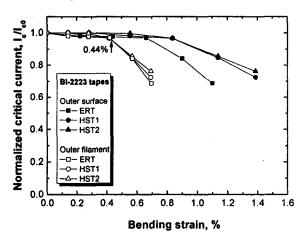


Fig. 3 I_c-ε_b dependence for all tapes.

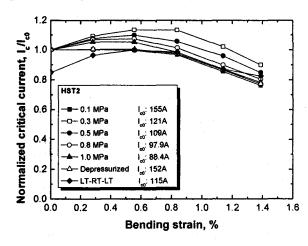


Fig 4. I_c degradation behaviors in HST2 Bi-2223 tape obtained from pressurization tests.

After pressurizing the tape up to 1 MPa, the pressure was released to atmospheric pressure and then the I_c was measured. The I_c was completely recovered to I_{c0} for all samples. It can be seen that pressurization of LN_2 up to 1 MPa did not cause any permanent damage to the filaments, although it is believed that it accelerated the diffusion of LN_2 into the multifilamentary bundle layer which eventually caused ballooning after a thermal cycle.

A thermal cycle was given to the samples after depressurization in order to investigate the influence of pressurization on the I_c degradation behavior. The result was added in Fig. 4 and represented by a diamond. It can be seen that I_c degraded at low applied bending strain regions which corresponds to the occurrence of ballooning in the sample. Ballooning was caused by the vaporization of LN₂, which diffused into the filaments, when the tape was warmed up to RT. This ballooning damage resulted in the significant degradation of I_c [2].

4. Conclusion

The Ic-Eb characteristics of externally-reinforced under pressurized LN_2 tapes Bi-2223 investigated. The tape with the thicker reinforcement showed a better bending strain tolerance of Ic when the bending strain was calculated at the outer surface, but when the bending strain was calculated at the outermost filament, the Ic degradation behavior became identical for all tapes. For all samples, Ico decreased with the increase of applied pressure. And when depressurized to atmospheric pressure from 1 MPa, the Ic completely recovered initial values at atmospheric pressure. when the samples Ballooning occurred warmed up to RT.

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